SL30N50T/SL30N50P

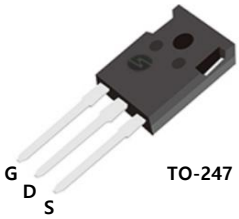
500V N-channel MOSFET

General Description

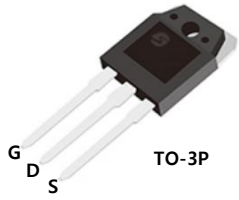
This Power MOSFET is produced using Slkor's advanced planar stripe DMOS technology.
This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.
These devices are well suited for AC/DC power conversion in switching mode operation for higher efficiency.

Features

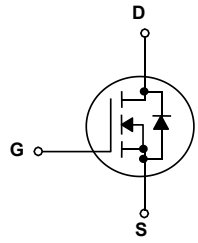
- 30A, 500V, $R_{DS(on)typ}$= 150mΩ@V_{GS} = 10 V
- Low gate charge (typical 72nC)
- Low Crss (typical 13pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



SL30N50T



SL30N50P



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter	SL30N50T	SL30N50P	Units
V_{DSS}	Drain-Source Voltage	500		V
I_D	Drain Current - Continuous (T_C = 25℃)	30		A
	- Continuous (T_C = 100℃)	20		A
I_{DM}	Drain Current - Pulsed (Note 1)	120		A
V_{GSS}	Gate-Source Voltage	±30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	430		mJ
P_D	Power Dissipation (T_C = 25℃)	278	298	W
	- Derate above 25℃	2.2	2.4	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		℃

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	SL30N50T	SL30N50P	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.45	0.42	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	℃/W

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	500	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 500 V, V_{GS} = 0 V	--	--	1	uA
		V_{DS} = 400 V, T_C = 125℃	--	--	10	uA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 uA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 15A	--	150	180	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 500kHz	--	4110	--	pF
C_{oss}	Output Capacitance		--	415	--	pF
C_{rss}	Reverse Transfer Capacitance		--	13	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 250 V, I_D =20A, R_G = 10 Ω (Note 3)	--	29	--	ns
t_r	Turn-On Rise Time		--	40	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	190	--	ns
t_f	Turn-Off Fall Time		--	41	--	ns
Q_g	Total Gate Charge	V_{DS} = 250 V, I_D =30A, V_{GS} = 10 V (Note 3)	--	72	--	nC
Q_{gs}	Gate-Source Charge		--	20	--	nC
Q_{gd}	Gate-Drain Charge		--	26	--	nC
R_G	Gate Resistance	f =1MHz	--	1.9	--	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--		30	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--		120	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 20A	--		1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 20A, dI_F / dt = 100 A/us	--	495	--	ns
Q_{rr}	Reverse Recovery Charge		--	7.8	--	uC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: T_J =25℃, V_{DD} =50V, V_G =10V, L=0.5mH,
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics

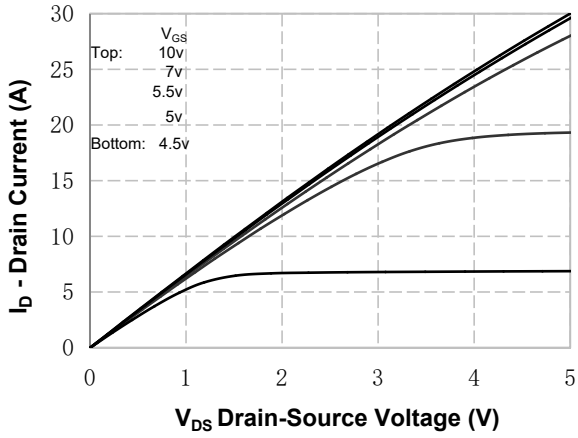


Figure 1. On-Region Characteristics

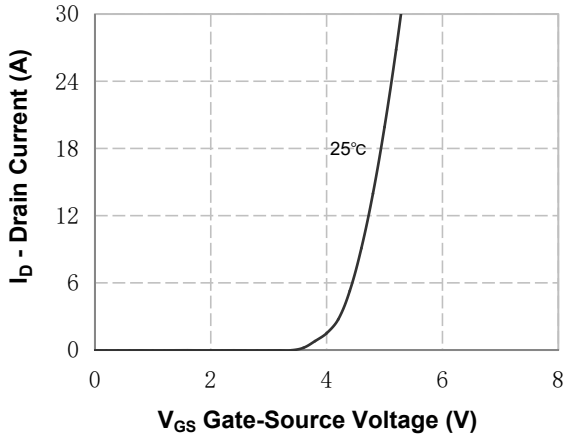


Figure 2. Transfer Characteristics

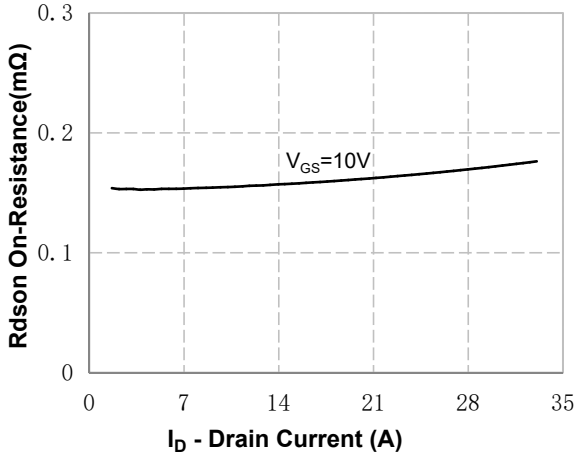


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

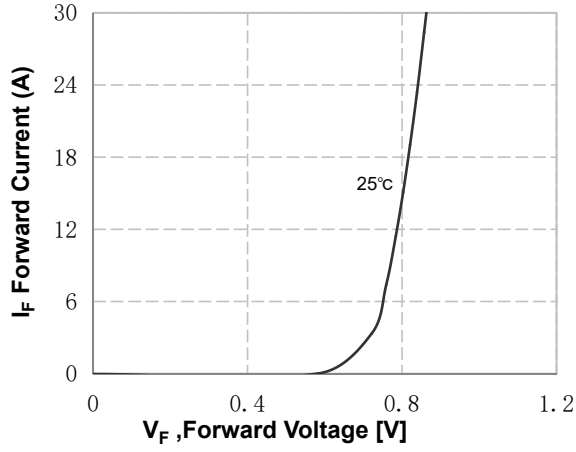


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

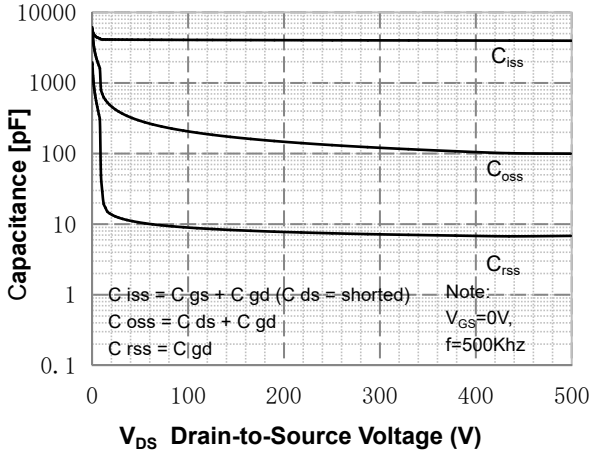


Figure 5. Capacitance Characteristics

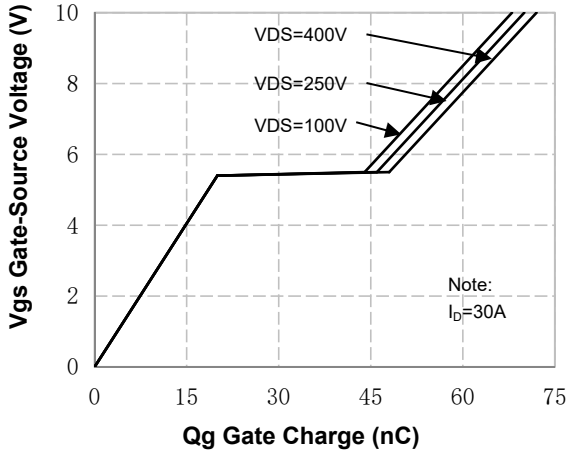


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

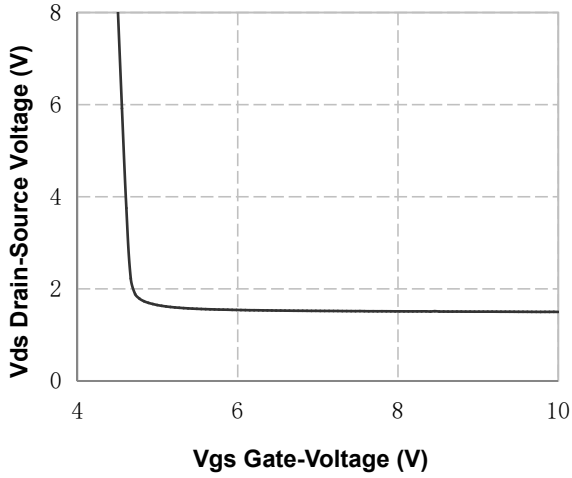


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

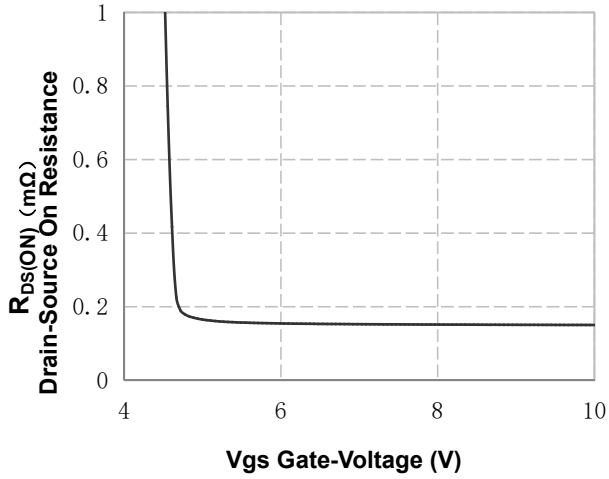


Figure 8. On-Resistance vs Gate Voltage

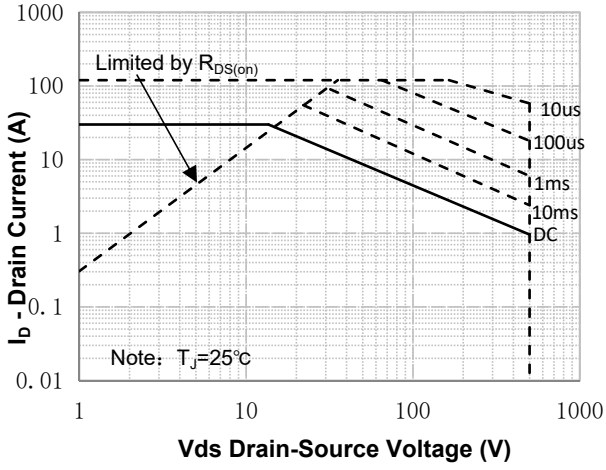


Figure 9. Maximum Safe Operating Area

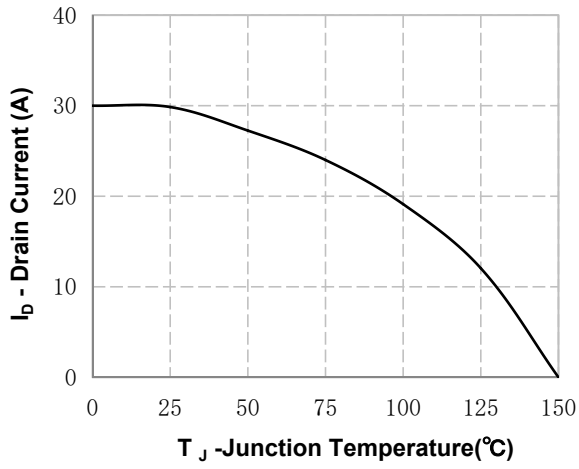


Figure 10. Maximum Drain Current vs Temperature

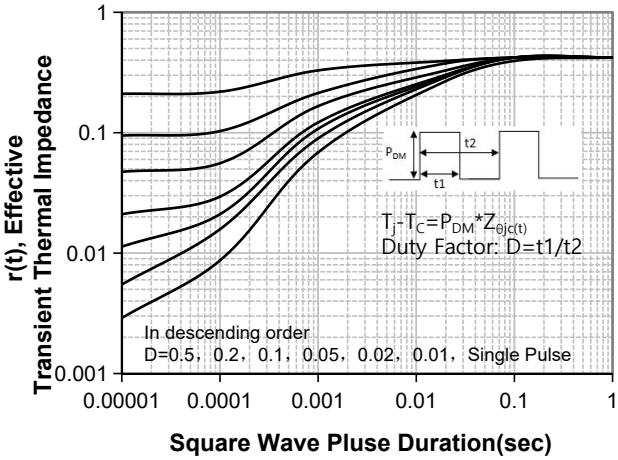
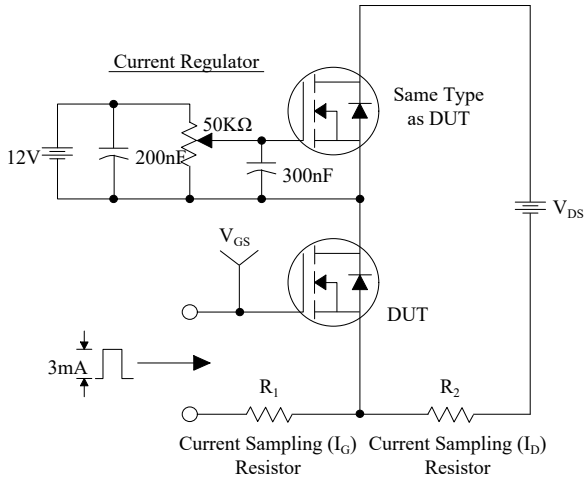
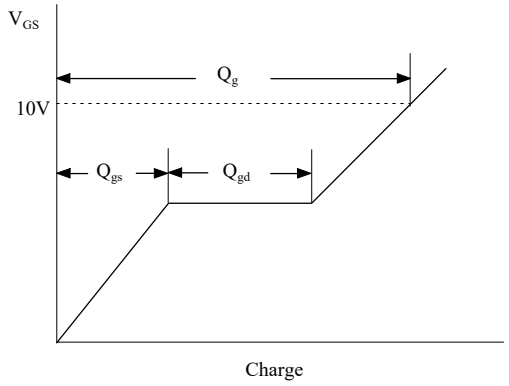


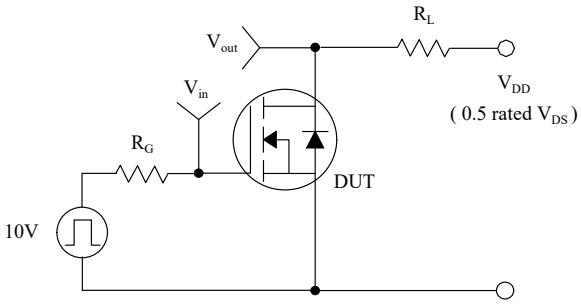
Figure 11. Transient Thermal Response Curve

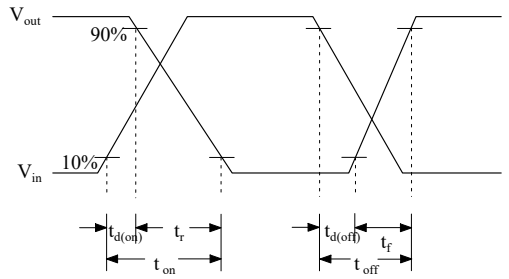
Gate Charge Test Circuit & Waveform



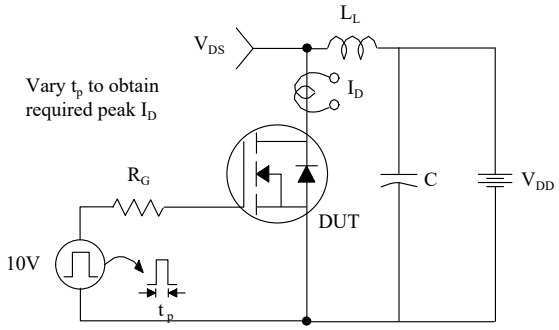


Resistive Switching Test Circuit & Waveforms

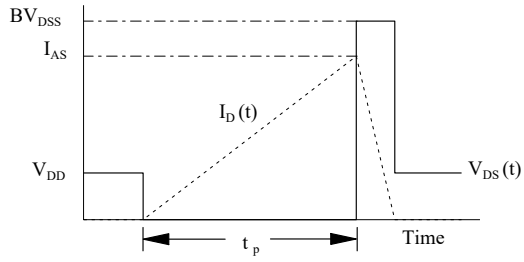




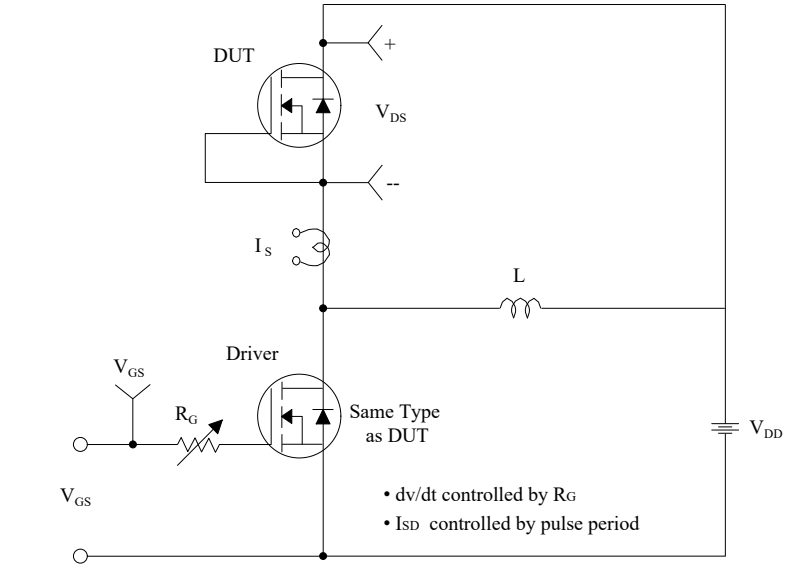
Unclamped Inductive Switching Test Circuit & Waveforms

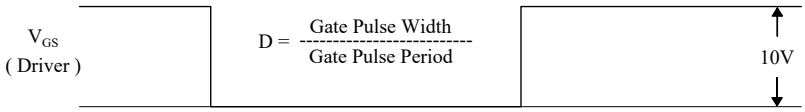


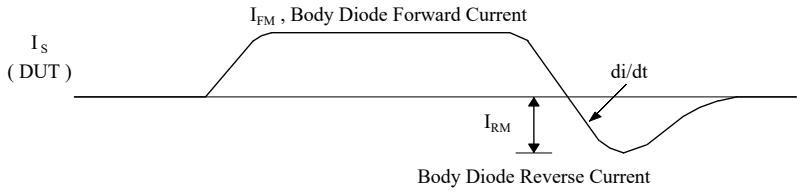
$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

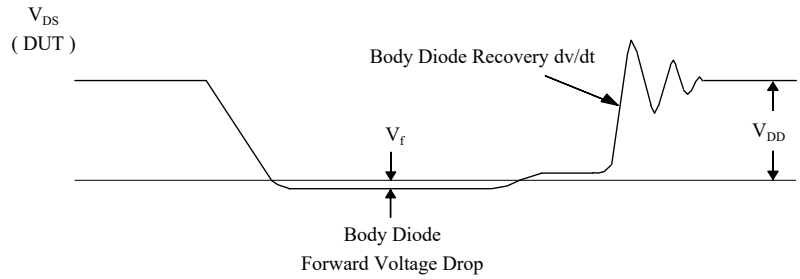


Peak Diode Recovery dv/dt Test Circuit & Waveforms

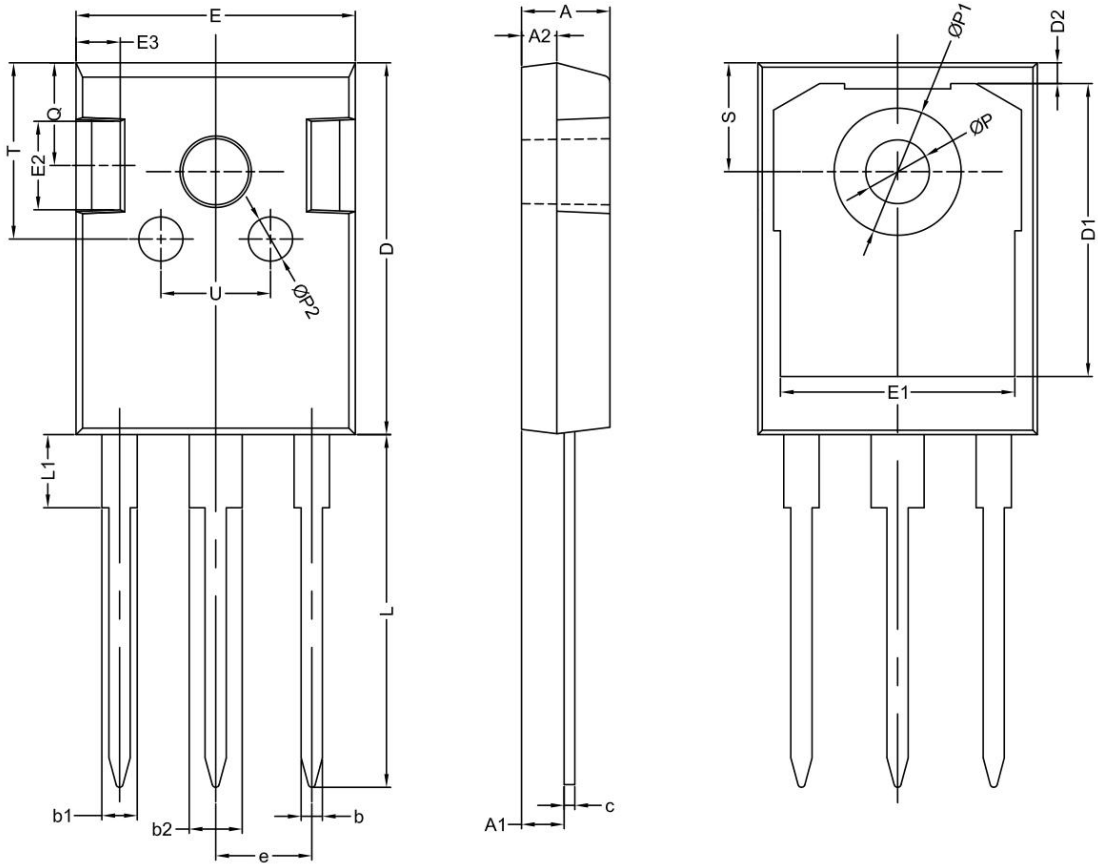








TO-247 OUTLINE

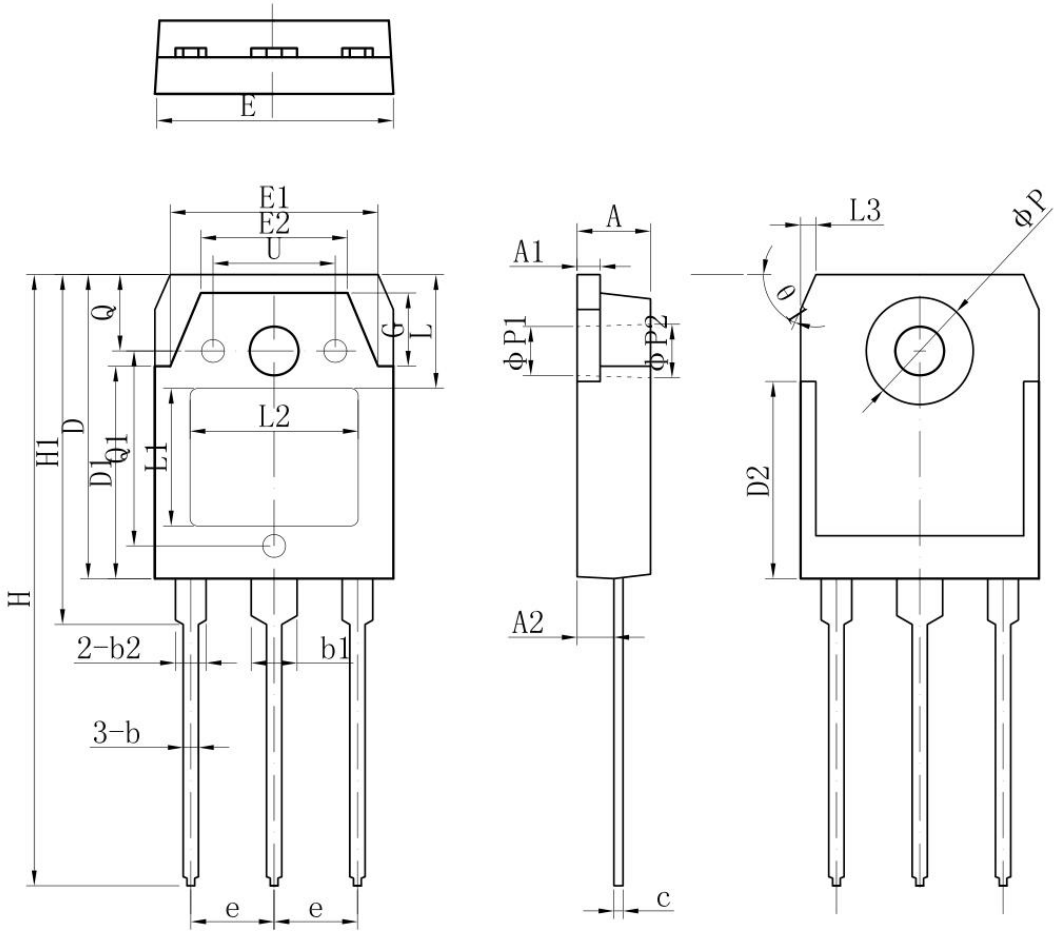


SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm		
	MIN	NOM	MAX						MIN	NOM	MAX
A	4.80	5.00	5.20	D	20.80	21.00	21.20	L1	-	4.13	-
A1	2.21	2.41	2.61	D1	-	16.55	-	⌀ P	3.5	3.6	3.7
A2	1.90	2.00	2.10	E	15.60	15.80	16.0	⌀ P1	-	-	7.40
b	1.10	1.20	1.35	E1		13.3		⌀ P2	-	2.50	-
b1	-	2.00	-	E2		5.0		Q	-	5.8	-
b2	-	3.00	-	e	5.44			S	6.05	6.15	6.25
c	0.55	0.60	0.75	L	19.42	19.92	20.42	T	-	10.0	-

NOTE：
1The plastic package is not marked as smooth surfaceRa=0.1;Subglossy surfaceR
a=0.8
2.Undeclared tolerance±0.15,Unmarked filletRmax=0.25

NAME	TO-247 OUTLINE	UNIT	mm	DESIGNED	Shawn	THIRD ANGLE SYSTEM
DWGNO		PAGE	1 OF 1	CHECKED		
VERSION	Ver1.0	ISSUE DATE		APPROVED		

TO-3P OUTLINE



SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm		
	MIN	NOM	MAX		MIN	NOM	MAX
A	4.6	4.8	5	E2		9.6	
A1	1.4	1.5	1.6	e		5.45	
A2	2.3	2.4	2.5	H	39.5	40	40.5
b	0.8	1	1.2	L	-	7.4	-
b1	2.9	3	3.25	L1	-	9	-
b2	1.9	2	2.25	L2	-	11	-
c	0.5	0.6	0.75	⌀ P	6.8	7	7.2
D	19.7	19.9	20.1	⌀ P1	-	3.2	-
E	15.4	15.6	15.8	Q1	-	12.76	-
E1		13.6		θ1	-	60°	-

NOTE：

1The plastic package is not marked as smooth surfaceRa=0.1;Subglossy surfaceRa=0.8

2.Undeclared tolerance±0.25,Unmarked filletRmax=0.25